

AMENDMENTS TO THE SPECIFICATION

Please amend the second paragraph on page 5 as follows:

Next, polysilicon layer 320 is conventionally doped. (Alternately, a doped layer of polysilicon can be formed in lieu of separate deposition and doping steps.) Following this, a layer of sacrificial oxide 330 is formed on polysilicon layer 320. Oxide layer 330 is also conformally formed and, like polysilicon layer 320, has a top surface 331 that has a number of substantially-equal lower levels 332 and a number of substantially-equal upper levels 334 that lie above the lower levels 332.